



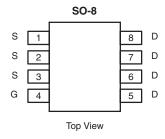
# N-Channel Reduced $Q_g$ , Fast Switching MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
30	0.0085 at V <sub>GS</sub> = 10 V	± 13		
	0.014 at V <sub>GS</sub> = 4.5 V	± 10		

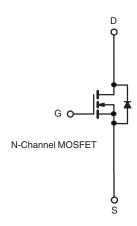
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETS
- High-Efficiency
- **PWM Optimized**
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4880DY-T1-E3 (Lead (Pb)-free)
Si4880DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	30	V		
Gate-Source Voltage		V <sub>GS</sub>	± 25	V		
Continuous Drain Current /T 150 °C\a.b	T <sub>A</sub> = 25 °C	1-	± 13			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 70 °C	l <sub>D</sub>	± 10			
Pulsed Drain Current (10 μs Pulse Width)		I <sub>DM</sub>	± 50	A		
Continuous Source Current (Diode Conduction) <sup>a, b</sup>		I <sub>S</sub>	2.3			
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.5	W		
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 70 °C		1.6	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	t ≤ 10 s	$R_{thJA}$		50	°C/W
	Steady State		70		C/VV

a. Surface mounted on FR4 board.

b.  $t \le 10 \text{ s}$ .

### **Si4880DY**

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MOSFET SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.8		1.8	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Coto Voltago Droin Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	1		1	4	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 13 A		0.0069	0.0085		
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A		0.0115	0.014	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 13 A		26		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.3, V <sub>GS</sub> = 0 V		0.70	1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			19.5	25		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 5.0 \text{ V}, I_{D} = 13 \text{ A}$		4.2		nC	
Gate-Drain Charge	Q <sub>gd</sub>			8.8			
Turn-On Delay Time	t <sub>d(on)</sub>			14	22		
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 15 \Omega$		9	15	ns	
Turn-Off DelayTime	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		46	70		
Fall Time	t <sub>f</sub>			30	45		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.3 A, dl/dt = 100 A/μs		35	70		

#### Notes:

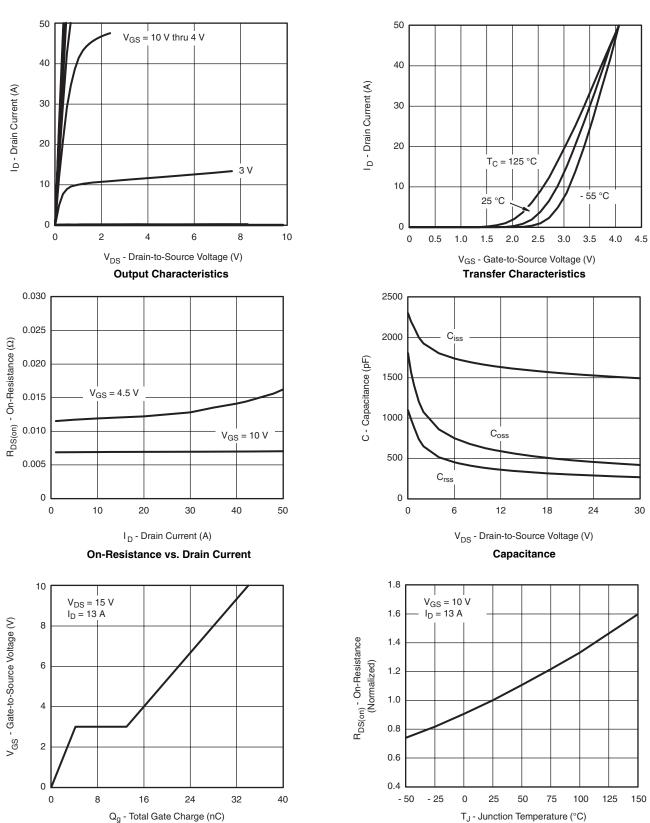
- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



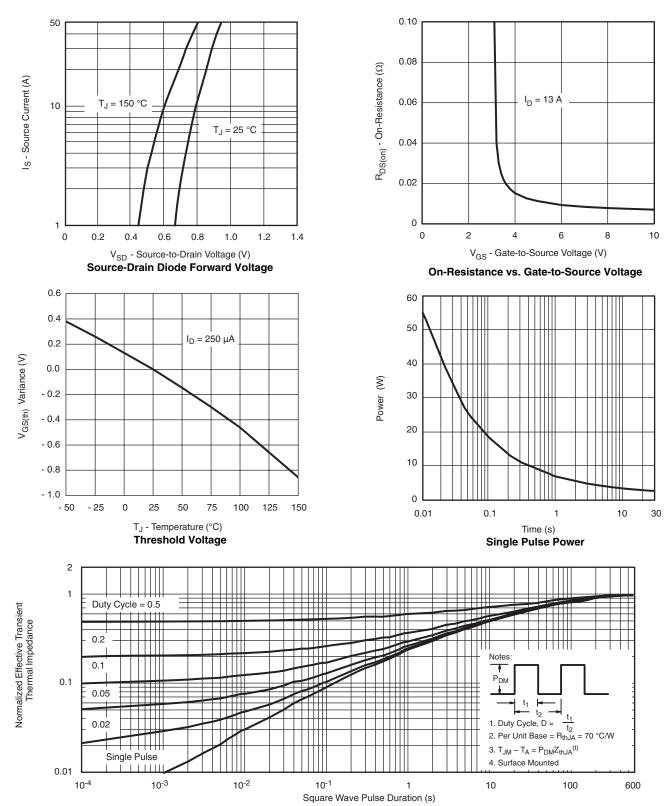
**Gate Charge** 

On-Resistance vs. Junction Temperature

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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